

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	119432	semiconductor and (cmos or complementary)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 15:51
L2	3412	1 and ((work adj function) or (fermi adj level))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 15:52
L3	1425	2 and (w or tungsten or zirconium or zr or hafnium or hf or vanadium or v or niobium or nb or titanium or ti or chromium or cr) and ((wn or (tungsten adj nitride)) or ((zirconium adj nitride) or zrn) or ((hafnium adj nitride) or hfn) or ((vanadium adj nitride) or vn) or ((niobium adj nitride) or nbn) or ((titanium adj nitride) or tin) or ((chromium adj nitride) or crn))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 16:09
L4	1064	3 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 16:09
L5	1056	4 and (insulat\$3 or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 16:10
L6	946	5 and different	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 16:10